L Number	Hits	Search Text	DB	Time stamp
1	9737	ald or atomic near2 layer near2 (epitax$5 or deposit$5) or ale	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/25 16:09
2	667	(ald or atomic near2 layer near2 (epitax$5 or deposit$5) or ale) and layer$5 near10 ratio	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/25 15:05
3	160	(ald or atomic near2 layer near2 (epitax$5 or deposit$5) or ale) same layer$5 near10 ratio	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/25 15:05
4	639	(ald or atomic near2 layer near2 (epitax$5 or deposit$5) or ale) same ("sio.sub.2" or silicon near2 (dioxide or oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/25 15:11
5	39	(ald or atomic near2 layer near2 (epitax$5 or deposit$5) or ale) same ("sio.sub.2" or silicon near2 (dioxide or oxide)) same ratio	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/25 15:13
6	12	1.ti. same ("sio.sub.2" or silicon near2 (dioxide or oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/25 15:13
7	83	1.ab. same ("sio.sub.2" or silicon near2 (dioxide or oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/25 15:15
8	337	(ald or atomic near2 layer near2 (epitax$5 or deposit$5) or ale) same (oxide and (multi$1compon$6 or multi$1layer or combinat$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/25 15:16
9	77	(ald or atomic near2 layer near2 (epitax$5 or deposit$5) or ale) near10 (oxide and (multi$1compon$6 or multi$1layer or combinat$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/25 15:16
10	86	(ald or atomic near2 layer near2 (epitax$5 or deposit$5) or ale) same (oxide and (multi$1compon$6 or multi$1layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/25 15:22
11	18	(ald or atomic near2 layer near2 (epitax$5 or deposit$5) or ale) same (oxide near10 (binary or tertiary))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/25 15:24
12	953	dielectric same (hemi$1spher$5) near2 grain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/25 15:25
13	261	(gate or capacitor) near2 dielectric same (hemi$1spher$5) near2 grain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/25 15:26
14	15	(gate or capacitor) near2 dielectric same (hemi$1spher$5) near2 grain near5 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/25 15:39

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15	1781	(gate or capacitor) near2 dielectric same electrode same (dram or dynamic near2 random near2 access near2 memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/25 15:40
16	341	(gate or capacitor) near2 dielectric near10 electrode near10 (dram or dynamic near2 random near2 access near2 memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/25 15:49
17	72	(gate or capacitor) near2 dielectric near2 electrode near5 (dram or dynamic near2 random near2 access near2 memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/25 15:50
18	24	(gate or capacitor) near2 dielectric near10 electrode near5 bottom near5 (dram or dynamic near2 random near2 access near2 memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/25 15:51
19	2	20040065253.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/25 16:00
20	40	(ald or atomic near2 layer near2 (epitax$5 or deposit$5) or ale) near10 silicate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/25 16:37
21	57	(eva near2 tois or suvi near2 haukka or marko near2 tuominen).in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/25 16:37
22	43	((eva near2 tois or suvi near2 haukka or marko near2 tuominen).in.) and (ald or atomic near2 layer near2 (epitax$5 or deposit$5) or ale)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/25 16:38
23	38	((eva near2 tois or suvi near2 haukka or marko near2 tuominen).in.) and (ald or atomic near2 layer near2 (epitax$5 or deposit$5) or ale) same oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/25 16:39
–	2	"20040065253"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/23 17:24
–	23	(ald or atomic near2 layer near2 (epitax$5 or deposit$5) or ale) same (multi$1compon$7)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/23 17:28
–	280	(ald or atomic near2 layer near2 (epitax$5 or deposit$5) or ale) same perovskite	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/23 17:28
–	14	(ald or atomic near2 layer near2 (epitax$5 or deposit$5) or ale) near10 perovskite	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/23 17:30
–	561	(ald or atomic near2 layer near2 (epitax$5 or deposit$5) or ale) same ("sio.sub.2" or sio2 or silicon near2 oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/23 17:31

-	242	(ald or atomic near2 layer near2 (epitax$5 or deposit$5) or ale) near20 ("sio.sub.2" or sio2 or silicon near2 oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/23 17:36
-	24	((ald or atomic near2 layer near2 (epitax$5 or deposit$5) or ale) near20 ("sio.sub.2" or sio2 or silicon near2 oxide)) and @py<2002	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/23 17:31
-	3	(ald or atomic near2 layer near2 (epitax$5 or deposit$5) or ale) near20 ("sio.sub.2" or sio2 or silicon near2 oxide) near20 combin$7	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/23 17:37
-	20	(ald or atomic near2 layer near2 (epitax$5 or deposit$5) or ale) same ("sio.sub.2" or sio2 or silicon near2 oxide) near20 combin$7	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/23 17:39
-	2901	alumina near2 silica near10 mineral	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/23 17:39
-	86	alumina near2 silica near10 mineral and @py=1997	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/23 17:39
-	717	87.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/23 17:49
-	38	87.ti. and 117$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 13:00
-	6	"87" same (multi$1layer$5 or multi$1compon$6) near5 oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 13:05
-	9737	ald or atomic near2 layer near2 (epitax$5 or deposit$5) or ale	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 13:03
-	33	(ald or atomic near2 layer near2 (epitax$5 or deposit$5) or ale) same (multi$1layer$5 or multi$1compon$6) near5 oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 13:07
-	669	(ald or atomic near2 layer near2 (epitax$5 or deposit$5) or ale) same silicon near5 oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 13:08
-	48	(ald or atomic near2 layer near2 (epitax$5 or deposit$5) or ale) same silicon near5 oxide and (silicon near2 tetrachloride or "sicl.sub.4")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 13:23
-	3	("6207487" | "6348386" | "6420279" | "2001/0024387" | "2001/0041250" | "2002/0004279" | "2002/0106536" | "2002/0146916" | "2002/0197881" | "2003/0040196" | "2003/0045048").PN.	USPAT	2004/09/24 13:13

–	7	(ald or atomic near2 layer near2 (epitax$5 or deposit$5) or ale) same silicon near5 oxide near10 (mix$5 or combinat$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 13:24
–	122	(ald or atomic near2 layer near2 (epitax$5 or deposit$5) or ale) and silicon near5 oxide near10 (mix$5 or combinat$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 13:31
–	130	(ald or atomic near2 layer near2 (epitax$5 or deposit$5) or ale) and "sio.sub.2" near10 (mix$5 or combinat$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 13:32
–	23	(ald or atomic near2 layer near2 (epitax$5 or deposit$5) or ale) same "sio.sub.2" near10 (mix$5 or combinat$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 15:52
–	114	(ald or atomic near2 layer near2 (epitax$5 or deposit$5) or ale) and ("hfcl.sub.4" or hafnium near2 tetrachloride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 15:59
–	26	(ald or atomic near2 layer near2 (epitax$5 or deposit$5) or ale) and ("hfcl.sub.4" or hafnium near2 tetrachloride) near10 oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 15:55
–	44	(ald or atomic near2 layer near2 (epitax$5 or deposit$5) or ale) same ("hfcl.sub.4" or hafnium near2 tetrachloride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 15:57
–	37	((ald or atomic near2 layer near2 (epitax$5 or deposit$5) or ale) same ("hfcl.sub.4" or hafnium near2 tetrachloride)) not ((ald or atomic near2 layer near2 (epitax$5 or deposit$5) or ale) and ("hfcl.sub.4" or hafnium near2 tetrachloride) near10 oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 15:56
–	69	("hfcl.sub.4" or hafnium near2 tetrachloride) near10 (hafnium near2 oxide or "hfo.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 15:57
–	107	((ald or atomic near2 layer near2 (epitax$5 or deposit$5) or ale) and ("hfcl.sub.4" or hafnium near2 tetrachloride)) not (((ald or atomic near2 layer near2 (epitax$5 or deposit$5) or ale) and ("hfcl.sub.4" or hafnium near2 tetrachloride) near10 oxide) and ((ald or atomic near2 layer near2 (epitax$5 or deposit$5) or ale) same ("hfcl.sub.4" or hafnium near2 tetrachloride)) and (("hfcl.sub.4" or hafnium near2 tetrachloride) near10 (hafnium near2 oxide or "hfo.sub.2")))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 16:04
–	7	"2332980"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 16:27
–	7	"si.sub.2cl.sub.6" same (ald or atomic near2 layer near2 (epitax$5 or deposit$5) or ale)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 16:28

-	24	"si.sub.2cl.sub.6" and (ald or atomic near2 layer near2 (epitax$5 or deposit$5) or ale)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 16:34
-	2111	hemispherical near2 grain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 16:34
-	55	(hemispherical near2 grain) near10 substrate same oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 17:10
-	424	capacitor near10 oxide near10 dynamic near5 memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 17:11
-	63	capacitor near10 oxide near10 dynamic near5 memory near10 electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 17:13
-	11	oxide near10 dynamic near5 random near2 memory near10 electrode near10 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 17:14
-	76	oxide near10 dynamic near5 random near2 memory near10 electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 17:18
-	741	capacitor near10 electrode near10 dynamic near5 random near2 memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 17:18
-	55	oxide near10 capacitor near10 electrode near10 dynamic near5 random near2 memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/25 15:03

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